NSN 5961-00-230-7559

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Inclosure Material:
Metal
Overall Length:
Between 0.170 inches and 0.210 inches
Terminal Length:
0.500 inches
Overall Diameter:
Between 0.209 inches and 0.230 inches
Internal Configuration:
Field effect
Electrode Internally-electrically Connected To Case:
Gate
Mounting Method:
Terminal
Terminal Circle Diameter:
0.100 inches
Features Provided:
Hermetically sealed case
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
40.0 drain to gate voltage and 40.0 drain to source voltage and 40.0 gate to source voltage
Current Rating Per Characteristic:
50.00 milliamperes gate current
Power Rating Per Characteristic:
1.8 watts total power dissipation
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius ambient air
Test Data Document:
81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specifica
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
3 uninsulated wire lead
Specification Data:
81349-mil-prf-19500/385 government specification
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
No
Fiig:

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Mil-std (military Standard):

Mil-prf-19500 spec.

